

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
215544US2SERIAL NO.
NEW APPLICATION

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Takuji MATSUMOTO, et al.

FILING DATE

Herewith

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	NO
	AO	8-228145	3/9/96	Japan (with Partial English Translation)		X
<i>A.S.</i>	AP	2000-243973	9/8/00	Japan (Corresponding to US Application No. 09/466,934)	 	X
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

<i>A.S.</i>	AW	S. MAEDA, et al. Impact of 0.18um SOI CMOS Technology using Hybrid Trench Isolation with High Resistivity Substrate on Embedded RF/Analog Applications, 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 154-155
	AX	
	AY	
	AZ	

Examiner

A.S.

Date Considered

9.13.02

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.